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Intrinsic Non-Radiative Voltage Losses in Fullerene-Based Organic Solar Cells

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Supplementary Notes

Supplementary Notes 1 - Theory of Voltage Losses

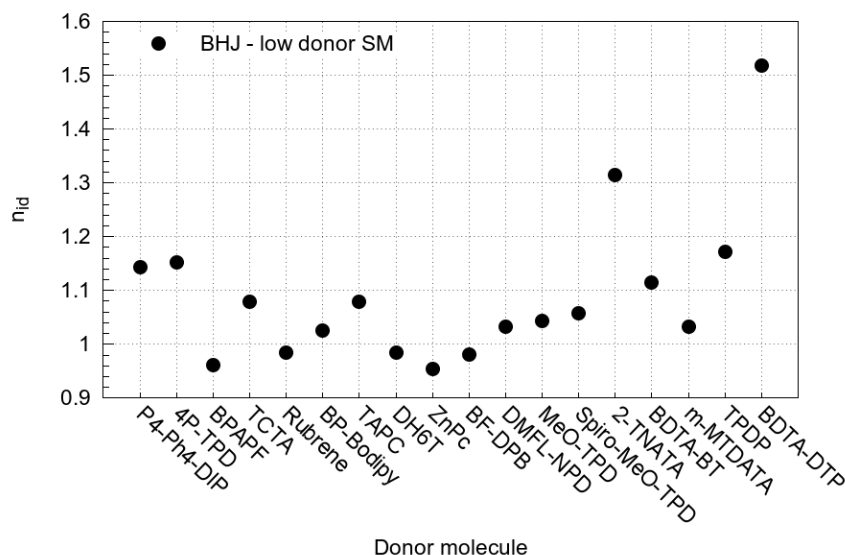
At open circuit, we assume detailed balance of generation (G) and recombination (R) rate ($G = R$), where all the recombination takes place via CT states:

$$G = kN_{CT}, \quad (1)$$

where k is the total recombination rate constant which is the sum of the radiative and the non-radiative recombination rate¹. N_{CT} is the density of populated CT states which can be described by:

$$N_{CT} = N_{CTC} \exp\left(\frac{-E_{CT} + qV_{OC}}{k_B T}\right), \quad (2)$$

with N_{CTC} as the density of CT states. Hereby, we assume in Supplementary Equation (1) that k is constant, implying that higher orders of recombination are neglected. The fact that the ideality for most of the studied systems was found to be close to unity, supports this assumption (see Supplementary Figure 1).



Supplementary Figure 1 | Ideality Factor n_{id} . Ideality factor of selected low donor OSCs comprised of 94 mol% of C_{60} and the noted donor molecule. The donor molecules are sorted with respect to the magnitude of the E_{CT} of the OSC, the highest E_{CT} is on the left side.

In OSCs, the non-radiative recombination rate is much larger than the radiative one. The recently highest reported EQE_{EL} for OSCs is about 10^{-4} ².

$$k = k_r + k_{nr} \approx k_{nr} \quad (3)$$

By rearranging Supplementary Equation (2), we get a relation for the V_{OC} :

$$qV_{\text{OC}} = E_{\text{CT}} + k_{\text{B}}T \ln\left(\frac{G}{k N_{\text{CTC}}}\right). \quad (4)$$

We identify the second term on the right side of Supplementary Equation (4) to the overall voltage losses (ΔV_{OC}) with respect to E_{CT} :

$$\Rightarrow \Delta V_{\text{OC}} = \frac{k_{\text{B}}T}{q} \ln\left(\frac{(k_{\text{r}}+k_{\text{nr}}) N_{\text{CTC}}}{G}\right) = V_{\text{OC}} - \frac{E_{\text{CT}}}{q}. \quad (5)$$

Furthermore, we can split ΔV_{OC} into radiative (ΔV_{r}) and non-radiative voltage losses (ΔV_{nr}):

$$q \Delta V_{\text{OC}} = k_{\text{B}}T \ln\left(\frac{k_{\text{r}}(k_{\text{r}}+k_{\text{nr}}) N_{\text{CTC}}}{G}\right), \quad (6)$$

$$q \Delta V_{\text{OC}} = k_{\text{B}}T \ln\left(\frac{k_{\text{r}}+k_{\text{nr}}}{k_{\text{r}}}\right) + k_{\text{B}}T \ln\left(\frac{k_{\text{r}} N_{\text{CTC}}}{G}\right) = q \Delta V_{\text{nr}} + q \Delta V_{\text{r}}. \quad (7)$$

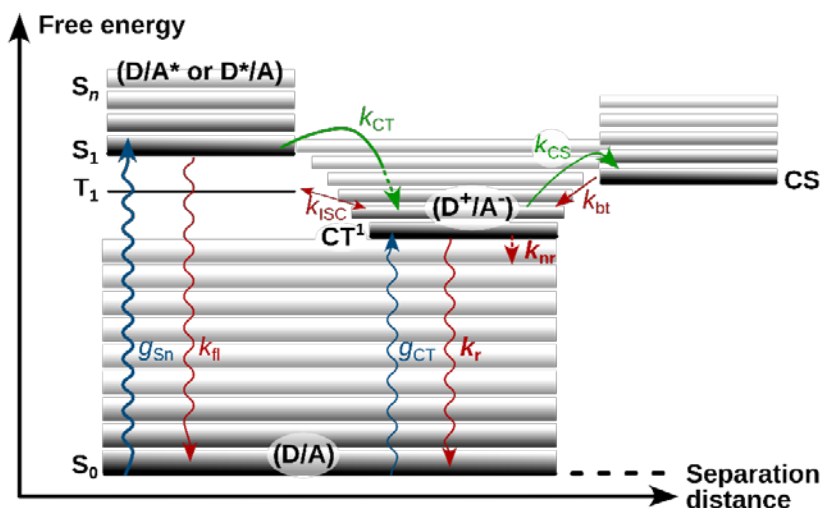
From Supplementary Equation (7) we can summarize the following relations, see Supplementary Table 1.

Supplementary Table 1 | Summary of Expressions for Voltage Losses in Excitonic SCs. The V_{OC} discussed in this paper refers, due the standard testing conditions of SCs, to an illumination of AM1.5G. $V_{\text{OC,rad}}$ equals the V_{OC} if only radiative recombination would take place.

Quantity	Definition by rates	Definition by SC characteristics
Overall voltage losses	$\Delta V_{\text{OC}} = \frac{k_{\text{B}}T}{q} \ln\left(\frac{(k_{\text{r}} + k_{\text{nr}}) N_{\text{CTC}}}{G}\right)$	$\Delta V_{\text{OC}} = E_{\text{CT}} - V_{\text{OC}} = \Delta V_{\text{r}} + \Delta V_{\text{nr}}$
Radiative voltage losses	$\Delta V_{\text{r}} = \frac{k_{\text{B}}T}{q} \ln\left(\frac{k_{\text{r}} N_{\text{CTC}}}{G}\right)$	$\Delta V_{\text{r}} = E_{\text{CT}} - V_{\text{OC,rad}}$
Non-radiative voltage losses	$\Delta V_{\text{nr}} = \frac{k_{\text{B}}T}{q} \ln\left(\frac{k_{\text{r}} + k_{\text{nr}}}{k_{\text{r}}}\right)$	$\Delta V_{\text{nr}} = V_{\text{OC,rad}} - V_{\text{OC}}$
Radiative efficiency	$EQE_{\text{EL}} = \frac{k_{\text{r}}}{k_{\text{r}} + k_{\text{nr}}} \approx \frac{k_{\text{r}}}{k_{\text{nr}}}$	$\Delta V_{\text{nr}} = \frac{k_{\text{B}}T}{q} \ln\left(\frac{1}{EQE_{\text{EL}}}\right)$

Supplementary Notes 2 - Simple Derivation of the “Energy-Gap Law” for Non-Radiative Recombination

At open circuit, a formed charge-transfer state (CT¹) can recombine either radiatively (k_{r}) or non-radiatively (k_{nr}) to the ground state (S_0). Free charges can recombine only if they form a state which is coupled to the ground state, which is by definition a CT state^{3,4}. Here, other decay possibilities such as intersystem crossing (k_{ISC}) to the triplet-excited state (T_1) or a back transfer to the singlet-excited state (S_1) are considered not to play a major role in the overall recombination⁵.



Supplementary Figure 2 | Scheme of the Electronic Structure of a D-A System. Upon an excitation of either the D or A (g_{S1}), the exciton can diffuse to the D-A interface where it creates a CT exciton. At open-circuit condition no charges (CS) are extracted, therefore, all charges have to recombine. This process is assumed to take place via the lowest energy state, the CT state, by radiative (k_r) and non-radiative (k_{nr}) recombination¹.

In what follows, we consider non-radiative decay from the CT state to the ground state as an electron transfer event, using Marcus theory and considering the presence of high frequency ($h\nu_v \approx k_B T$) and low frequency ($h\nu_s \ll k_B T$) vibrations. In electron transfer studies in solutions, the low frequency vibrations are referred to as solvent vibrations^{6, 7}, we attribute these vibrations to the deformation of the entire donor and acceptor molecule upon charging⁸. Since the energy spacing of these vibrations is very small, we can treat them classically^{6, 7}. On the other hand, the high frequency vibrations represent skeletal vibrations, which are treated here with a mean vibrational mode ($\bar{\nu}_v$) to keep the description as simple as possible. An electron transfer from the excited state ($i = 0$), the CT state, to the ground state (j) is proportional to the Franck-Condon overlap factor (FC), given by the sum of overlapping wave-functions of the CT state with all possible vibrational modes of the ground state ($j = \{0, 1, 2, \dots\}$)^{9, 7}. Using the Franck-Condon theory thereby includes the Born-Oppenheimer approximation.

$$FC(g) = (4\pi\lambda_s k_B T)^{-1/2} \sum_{j=0}^{\infty} \frac{\exp(-S) S^j}{j!} \cdot \exp\left[-\frac{(g - jh\bar{\nu}_v - \lambda_s)^2}{4\lambda_s k_B T}\right]. \quad (8)$$

S represents the ratio of the high frequency relaxation energy (λ_v) and the mean phonon-energy $h\bar{\nu}_v$ ($S = \frac{\lambda_v}{h\bar{\nu}_v}$). The rate of non-radiative electron-transfer can be written as⁷:

$$k_{nr} = \frac{4\pi}{h} V^2 FC(g = E_{CT}), \quad (9)$$

where g is the free energy for the non-radiative transition and equivalent to E_{CT} . To approximate the dependence of k_{nr} on E_{CT} , we evaluate FC . First, we consider that the Gaussian term in Supplementary Equation (8) is maximal if j equals j_{max} .

$$E_{CT} - jh\bar{\nu}_v - \lambda_s = 0 \quad (10)$$

$$\Rightarrow j_{max} = \frac{E_{CT} - \lambda_s}{h\bar{\nu}_v} \quad (11)$$

The index j_{max} clearly depends on E_{CT} . For typical values of E_{CT} , λ_s , and $h\bar{\nu}_v$ of our material system, we get $j = \{0.5 \dots 8\}$. We apply the Stirling approximation to evaluate the basic dependence of $\sum_{j=0}^{\infty} \frac{\exp(-S) S^j}{j!}$ on E_{CT} .

$$k_{nr} \propto \sum_{j=0}^{\infty} \frac{\exp(-S) S^j}{j!} \approx \sum_{j=0}^{\infty} \frac{\exp(-S) S^j}{\exp[j \ln(j) - j]} = \sum_{j=0}^{\infty} \exp[-S] \exp[j \ln(S)] \exp[-(j \ln(j) - j)] \quad (12)$$

Since the summand of FC with $j = j_{max}$ has the biggest contribution, we are going to consider only this term:

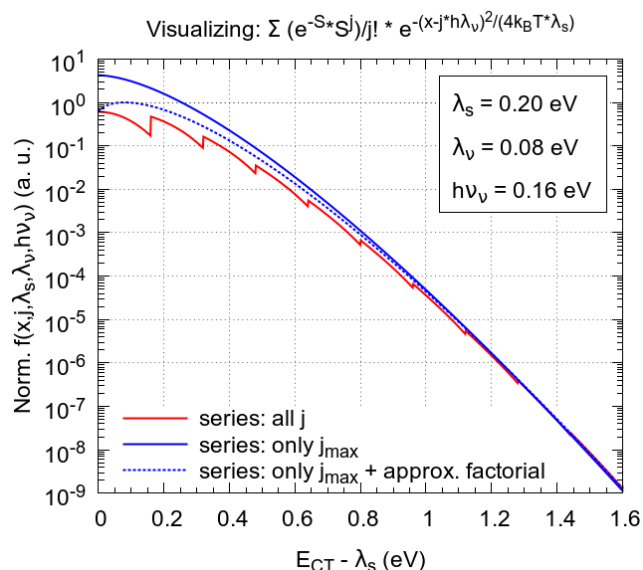
$$k_{nr} \propto \exp[-S] \exp[j_{max} \ln(S)] \exp[-(j_{max} \ln(j_{max}) - j_{max})] \quad (13)$$

$$\Rightarrow k_{nr} \propto \exp \left[j_{max} \left\{ \ln \left(\frac{S}{j_{max}} \right) + 1 \right\} - S \right] \quad (14)$$

$$\rightarrow k_{nr} \propto \exp \left[\frac{E_{CT} - \lambda_s}{h\bar{\nu}_v} \left\{ \ln \left(\frac{\lambda_v}{E_{CT} - \lambda_s} \right) + 1 \right\} - \frac{\lambda_v}{h\bar{\nu}_v} \right] \quad (15)$$

$$\rightarrow k_{nr} \propto \exp \left[-\frac{E_{CT} - \lambda_s}{h\bar{\nu}_v} \left\{ \ln \left(\frac{E_{CT} - \lambda_s}{\lambda_v} \right) - 1 \right\} - \frac{\lambda_v}{h\bar{\nu}_v} \right]. \quad (16)$$

To simplify FC to Supplementary Equation (16) we consider only the highest vibrational mode of the ground state, i.e. j_{max} , and we simplify the factorial of j as described in Supplementary Equation (12). Supplementary Figure 3 visualizes that these two approximations are very reasonable for further analyses.



Supplementary Figure 3 | Approximating the Franck-Condon Overlap Factor. The Franck-Condon Overlap Factor in Supplementary Equation (8) is simplified by considering only the highest vibrational mode of the ground state, j_{\max} , and approximating the factorial of j as described in the text. As indicated by the dashed blue line, the approximations are reasonable.

According to Gould et al. 1993⁷, we can express the radiative recombination rate constant as:

$$k_r = \frac{64\pi^2}{3h^3c^3} n^3 \bar{\nu}_v V^2 \Delta \mu^2, \quad (17)$$

with $h\bar{\nu}_v = E_{CT} - \lambda_s - \lambda_v$. Here, n is the refractive index of the material, V is the matrix coupling element of both energy states, $\bar{\nu}_v$ is the mean frequency of emission⁷, and $\Delta \mu$ is the difference of the dipole moment of both energy states.

Since both the non-radiative and the radiative decay rate depend on the electronic coupling matrix, $k_r, k_{nr} \propto V^2$, we choose the quantity of the quantum efficiency of emission (EQE_{EL}) which cancels out the dependency of the electronic coupling.

$$EQE_{EL} \propto \frac{k_r}{k_r + k_{nr}} \approx \frac{k_r}{k_{nr}} \quad (18)$$

Finally, with these approximations we get the following relation for the EQE_{EL} :

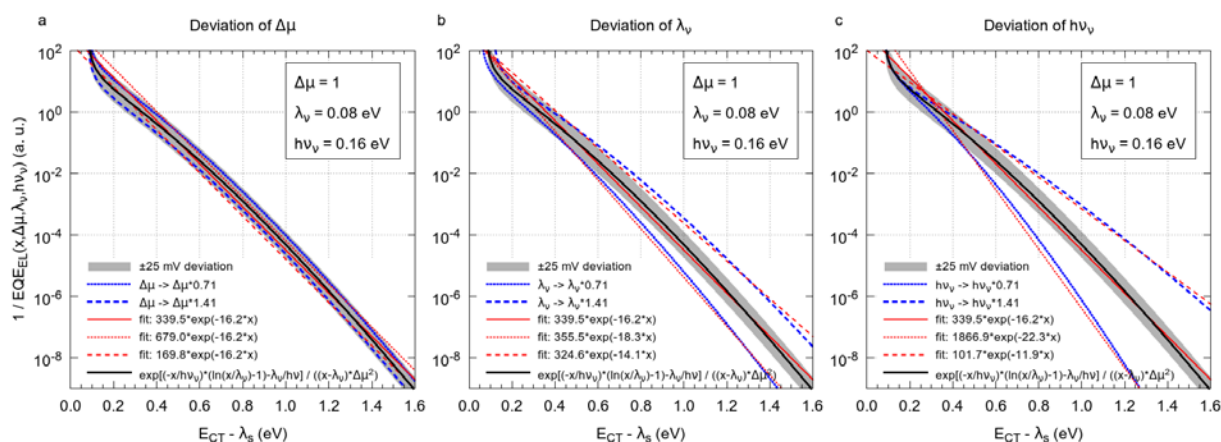
$$EQE_{EL} \propto \frac{\Delta \mu^2 (E_{CT} - \lambda_s - \lambda_v)}{\exp\left[-\frac{E_{CT} - \lambda_s}{h\nu_v} \left\{ \ln\left(\frac{E_{CT} - \lambda_s}{\lambda_v}\right) - 1 \right\} - \frac{\lambda_v}{h\nu_v}\right]}. \quad (19)$$

We see that EQE_{EL} strongly scales with $E_{CT} - \lambda_s$. From the experimental point of view, the non-radiative voltage losses ($\Delta V_{nr} = -\frac{k_B T}{q} \ln(EQE_{EL})$) represent a fundamental important quantity, for which we find the following dependency:

$$\Rightarrow \Delta V_{\text{nr}} \propto -\frac{k_{\text{B}}T}{q} \cdot \left[\frac{E_{\text{CT}} - \lambda_{\text{s}}}{h\bar{\nu}_{\text{v}}} \left\{ \ln \left(\frac{E_{\text{CT}} - \lambda_{\text{s}}}{\lambda_{\text{v}}} \right) - 1 \right\} + \frac{\lambda_{\text{v}}}{h\bar{\nu}_{\text{v}}} \right] \quad (20)$$

$$\Rightarrow \Delta V_{\text{nr}} \propto -\frac{k_{\text{B}}T}{q} \left[\frac{E_{\text{CT}} - \lambda_{\text{s}}}{h\bar{\nu}_{\text{v}}} \right] \quad (21)$$

Supplementary Equation (21) is a well known relation and in the literature and referred to as the “Energy-Gap law”^{9, 7, 10, 11}. This approximation assumes that the difference of the dipole moments $\Delta\mu$, the relaxation energy of the high energy vibrations λ_{v} , and the typical mean phonon-energy of the high frequency vibrations $h\bar{\nu}_{\text{v}}$ are rather constant for all materials in this study. To visualize the impact of possible variations of these parameters, Supplementary Figure 4a-c shows a deviation of each parameter by a factor of 2. The black line shows the reciprocal of Supplementary Equation (19), with $x = E_{\text{CT}} - \lambda_{\text{s}}$, which describes the physical model the best, the grey area indicates a deviation of the black line by ± 25 mV, assuming room temperature. The red solid line is a corresponding exponential fit of Supplementary Equation (19) which is very reasonable in the domain of x -values used in this study. A variation of $\Delta\mu$ would lead only to a relatively small vertical deviation, however, the slope of the relation does not change as shown by Supplementary Figure 4a. If λ_{v} would change by a factor 2, especially higher x -values would be influenced and the slope would deviate by $\sim 30\%$, see Supplementary Figure 4b. A deviation in the typical mean phonon-energy $h\bar{\nu}_{\text{v}}$ would directly change the slope of relation as shown in Supplementary Figure 4c.



Supplementary Figure 4 | Error Analyses for Approximating the Energy-Gap Law. The Supplementary Equation (19) is simplified to Supplementary Equation (21) by assuming that $\Delta\mu$, λ_{v} , and $h\nu_{\text{v}}$ are rather constant for all investigated materials. **a-c** show a variation of each parameter by a factor of 2. The black curve represents the reciprocal of Supplementary Equation (19) for typical values, given in the upper right corner of the plot, and the grey area a corresponding variation of ± 25 mV. The blue dashed lines correspond to reciprocal of Supplementary Equation (19) with the variation of one parameter by a total factor of 2. Red lines show exponential fits to the curves having the same line type.

In Figure 3a in the main text, we observe a trend where the ΔV_{nr} changes by about 255 mV from $x = (0.2 \text{ to } 1.4) \text{ eV}$ which equals a change of EQE_{EL} by $\sim 3 \cdot 10^5$. The experimental data is scattered

which can be mainly explained by moderate deviations of $\Delta\mu$ and λ_v which would mainly cause scattering in the height of single ΔV_{nr} values. However, the observation of a clear trend indicates that $h\bar{\nu}_v$ has to be quite constant over all molecules, otherwise a trend would not be visible.

Supplementary Notes 3 - Impact of Intrinsic Non-Radiative Recombination on the Maximum *PCE* of OSCs

The Shockley-Queisser (SQ) or detailed balance limit for the *PCE* of a single junction SC with an optical gap E_g makes the following assumptions¹²:

- (i) Perfect absorption of photons with energy E higher than the optical gap E_g , with each photon creating exactly one electron-hole pair. The absorption for photons with energy $E < E_g$ is zero.
- (ii) Perfect separation and collection of charge carriers, i.e. perfect internal quantum efficiency (*IQE*), which requires mobility-times-lifetime products much larger than the device thickness and the absence of geminate recombination.
- (iii) Radiative, i.e. non-geminate, recombination is the only allowed recombination mechanism. In other words, the EQE_{EL} equals to one.

In what follows, we re-derive the SQ limit¹², and adjust it for OSCs. Point (i) and (ii) assume that EQE_{PV} equals 100% for photon energies higher than E_g , while it is zero below E_g . With respect to this assumption, the maximum obtainable photocurrent under AM1.5G illumination with photon-flux spectrum $\varphi_{AM1.5G}(E)$ can be calculated:

$$j_{ph}^{SQ}(E_g) = q \int_0^{+\infty} EQE_{PV}(E) \varphi_{AM1.5G}(E) dE = q \int_{E_g}^{+\infty} \varphi_{AM1.5G}(E) dE \quad (22)$$

For inorganic SCs, such as GaAs and Si, EQE_{PV} values well over 90% have been demonstrated. For OSCs, some D:A blends were demonstrated to have *IQE* values close to 100%¹³, resulting in EQE_{PV} values of about 80-90% above the optical gap E_g of the main absorber. Therefore, the j_{SC} is rather close to the theoretical maximum for both inorganic SCs and the best OSCs.

Due to assumption (iii) recombination occurs only via radiative recombination. Assuming the reciprocity between absorption and emission¹⁴ and that the absorption is negligible below the optical gap (i) the recombination current density $j_{rec}(V)$ can be calculated:

$$j_{rec}(V) = j_0^{SQ} \left(\exp\left(\frac{qV}{k_B T}\right) - 1 \right) \quad (23)$$

with:

$$j_0^{SQ}(E_g, T) = q \int_0^{+\infty} EQE_{PV}(E) \varphi_{BB}(E, T) dE = q \int_{E_g}^{+\infty} \varphi_{BB}(E, T) dE \quad (24)$$

with $\varphi_{\text{BB}}(E, T)$ the black body spectrum. Since the total current density is the sum of j_{ph} and j_{rec} , an expression for the current-voltage $j(V)$ relationship under the assumptions (i)-(iii) can be derived^{12, 15, 16, 17}:

$$j(V) = j_0 \left(\exp\left(\frac{qV}{k_{\text{B}}T}\right) - 1 \right) - j_{\text{ph}}. \quad (25)$$

The maximum V_{OC} is then given by:

$$V_{\text{OC}}^{\text{SQ}} = \frac{k_{\text{B}}T}{q} \ln\left(\frac{j_{\text{ph}}^{\text{SQ}}}{j_0^{\text{SQ}}} + 1\right). \quad (26)$$

Our work shows that assumption (iii) is violated for OSCs, with EQE_{EL} being substantially lower than one, due to the presence of unavoidable intermolecular vibrational modes. Together with electron transfer losses, the additional non-radiative recombination results in a decreased V_{OC} , which depends on E_{g} :

$$V_{\text{OC}}(E_{\text{g}}, \Delta(E_{\text{g}})) = V_{\text{OC}}^{\text{SQ}}(E_{\text{g}}) - \Delta(E_{\text{g}}). \quad (27)$$

For a jV -curve given by Supplementary Equation (25), the following recursive formulas relate the V_{OC} to the fill factor (FF):

$$FF = \frac{\left(\frac{qV_{\text{MPP}}}{k_{\text{B}}T}\right)^2}{\left(1 + \frac{qV_{\text{MPP}}}{k_{\text{B}}T} - \exp\left(-\frac{qV_{\text{MPP}}}{k_{\text{B}}T}\right)\right)\left(\frac{qV_{\text{MPP}}}{k_{\text{B}}T} + \ln\left(1 + \frac{qV_{\text{MPP}}}{k_{\text{B}}T}\right)\right)}, \quad (28)$$

with:

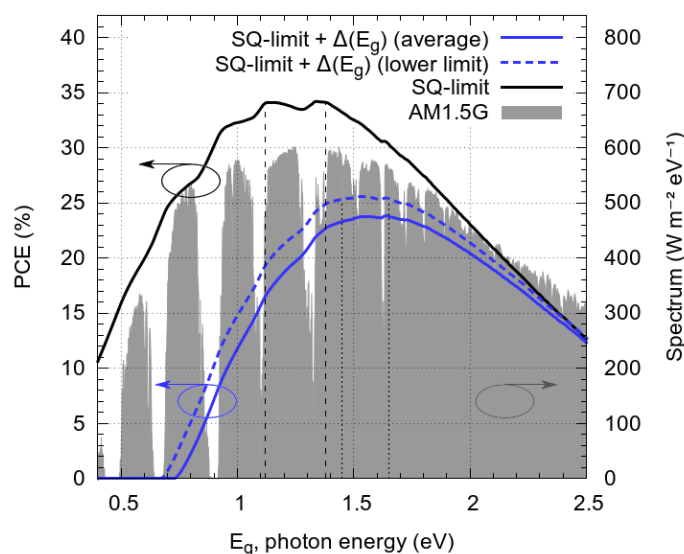
$$V_{\text{OC}}(E_{\text{g}}, \Delta(E_{\text{g}})) = V_{\text{MPP}} + \frac{k_{\text{B}}T}{q} \ln\left(1 + \frac{qV_{\text{MPP}}}{k_{\text{B}}T}\right). \quad (29)$$

Now we have expressions for the maximum j_{SC} , the V_{OC} , and the FF which allows us to set an upper limit for the PCE as a function of $\Delta(E_{\text{g}})$.

$$PCE(E_{\text{g}}, \Delta(E_{\text{g}})) = j_{\text{SC}}(E_{\text{g}}) \cdot V_{\text{OC}}(E_{\text{g}}, \Delta(E_{\text{g}})) \cdot FF(E_{\text{g}}, \Delta(E_{\text{g}})) \quad (30)$$

If Δ equals zero, we are in the SQ limit. However, for OSCs we have to adjust the detailed balance limit, since Δ will never be negligible due to the intrinsic non-radiative recombination which follows the EGL. Since it has been shown that the electron transfer losses can be reduced to rather low values <50 meV, still keeping the IQE rather high^{18, 2, 19, 20}, these voltage losses do not seem to be fundamental. However, as we demonstrate in this work, the voltage losses due to non-radiative recombination are intrinsic, obeying an EGL with a simplified relation:

$$\Delta(E_{\text{g}}) = \frac{k_{\text{B}}T}{q} \ln\left(\frac{1}{EQE_{\text{EL}}}\right) = A - B \cdot E_{\text{g}}. \quad (31)$$



Supplementary Figure 5 | Upper Limit for PCE as a Function of the Optical Gap and Additional Voltage Losses.

Maximum *PCE* of a single junction SC under the assumptions (i)-(iii) as a function of the optical gap (E_g), shown as solid black line. The maximum *PCE* of OSCs is reduced due to intrinsic non-radiative voltage losses $\Delta(E_g)$. The dashed blue line represents the minimal amount of intrinsic voltage losses which are found to be typical for OSCs, therefore, the highest, theoretical *PCE* for OSCs reduces to about 25.5%. The solid blue line shows the average losses obtained in this study. The intrinsic non-radiative voltage losses $\Delta(E_g)$ cause a blue-shift of the optimal optical gap (E_g), indicated by vertical dashed lines, from (1.12-1.38) eV to (1.45-1.65) eV. The filled grey curve represents the AM1.5G sun spectrum as a function of the photon energy.

Taking into account Supplementary Equation (31), we derive a corrected upper limit for the *PCE* of OSCs, shown in Supplementary Figure 5 as blue lines. *PCEs* below the dotted blue line are in principle reachable, the limiting case is described by an EQE_{PV} of 100% above the optical gap of the main absorber and no electron transfer losses. *PCEs* above the dotted blue line are found to be not reachable for OSCs. The highest *PCE* of 25-26% is achieved for absorber molecules with an E_g of (1.45-1.65) eV. The V_{OC} for these devices with an optimized optical gap and assuming no electron transfer losses but following the EGL is accordingly (0.93-1.17) V.

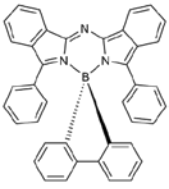
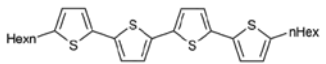
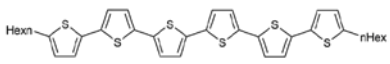
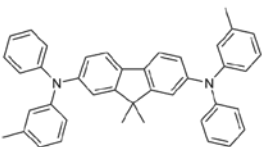
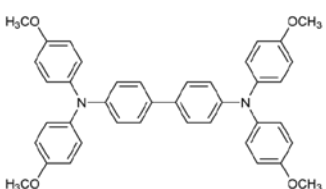
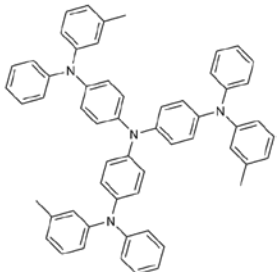
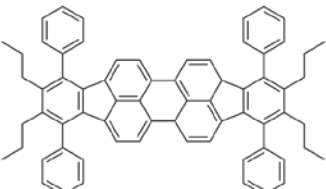
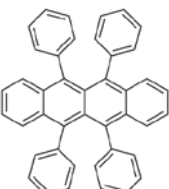
One of the currently best OSCs²¹ has an optical gap of about 1.65 eV, a V_{OC} of 0.78 V, and an *FF* of 73% resulting in a *PCE* of 11.7%. This device has an EQE_{PV} of 83-86%. If we could optimize the voltage of this device by decreasing the electron transfer losses, the unavoidable non-radiative losses would limit the possible *PCE* to about 17.6%.

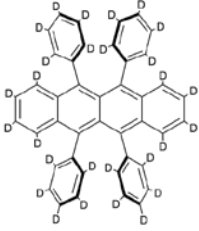
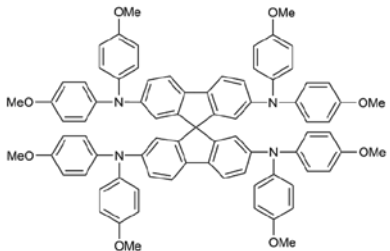
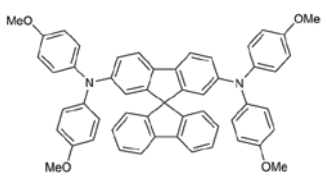
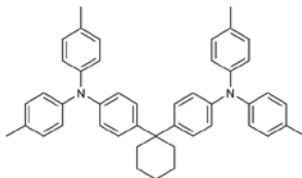
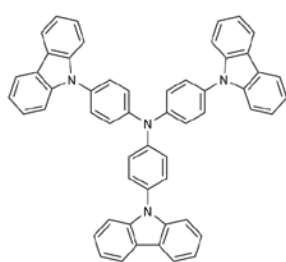
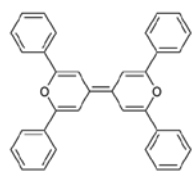
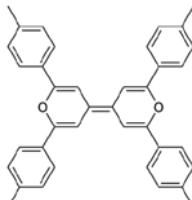
Up to now, OSCs with an EQE_{PV} of 85%²¹ and *FF* of 80%²² have been demonstrated. For an absorber with an optimal E_g , the maximum *PCE* for such a device would amount 19.5% by taking the intrinsic non-radiative voltage losses into account. This optimal E_g is (1.52-1.54) eV, resulting in a maximal V_{OC} of (1.01-1.04) V.

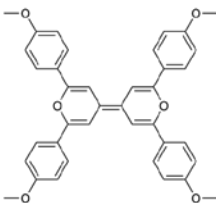
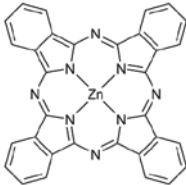
Supplementary Tables

Supplementary Table 2 | Overview of Used Donor Materials and Their Suppliers.

No.	Short Name	Chemical Structure	Long Name	Supplier
1	2-TNATA		4,4',4''-tris(2-naphthylphenylamino)-triphenylamine	Sensient
2	4P-TPD		4,4'''-bis(<i>N,N</i> -ditphenylamino)-1,1':4',1'':4'',1'''-quaterphenyl	Sensient
3	α -6T		2,2':5',2'':5'',2''':5''',2''''-5''''-sexithiophene	Lumtec
4	BDTA-BT		5,5'-bis(<i>N,N</i> -di- <i>p</i> -tolylamino)-2,2'-bithiophene	Georgia Institute of Technology
5	BDTA-DTP		<i>N</i> -(4- <i>tert</i> -butylphenyl)-2,6-bis(<i>N,N</i> -di- <i>p</i> -tolylamino)dithieno[3,2- <i>b</i> ;2',3'- <i>d</i>]pyrrole	Georgia Institute of Technology
6	BF-DPB		<i>N,N'</i> -diphenyl- <i>N,N'</i> -bis(9,9-dimethylfluoren-2-yl)-benzidine	Synthon
7	BPAPF		9,9-bis[4-(<i>N,N</i> -bis-biphenyl-4-yl-amino)phenyl]-9 <i>H</i> -fluorene	Lumtec

8	BP-Bodipy		10',14'-diphenyl5λ ⁴ ,11λ ⁴ spiro[dibenzo[<i>b,d</i>]borole-5,12'-[1,3,5,2]1,3,5,2]triazaborinino[4,3- <i>a</i> :6,1- <i>a'</i>]diisoindole]	TU Dresden
9	DH4T		5,5''''-dihexyl-2,2':5',2'':5'',2'''-quarterthiophene	University Ulm
10	DH6T		5,5''''-dihexyl-2,2':5',2'':5'',2'''-sexithiophene	University Ulm
11	DMFL-NPD		9,9-dimethyl- <i>N,N'</i> -diphenyl- <i>N,N'</i> -di- <i>m</i> -tolyl-9 <i>H</i> -fluorene-2,7-diamine	Lumtec
12	MeO-TPD		<i>N,N,N',N'</i> -tetrakis(4-methoxyphenyl)-benzidine	Sensient
13	m-MTDATA		4,4',4''-tris(3- <i>m</i> -tolyl-phenylamino)-triphenylamine	Lumtec
14	P4-Ph4-DIP		2,3,10,11-tetrapropyl-1,4,9,12-tetraphenyl-diindeno[1,2,3- <i>cd</i> :1',2',3'- <i>lm</i>]perylene	TU Dresden
15	Rubrene		5,6,11,12-tetraphenyl-tetracene	Sensient

16	Rubrene D ₂₈		5,6,11,12-tetrakis(phenyl- <i>d</i> ₅)tetracene-1,2,3,4,7,8,9,10- <i>d</i> ₈	University Minnesota Twin Cities
17	Spiro-MeO-TAD		2,2',7,7'-tetrakis[<i>N,N</i> -di(4-methoxyphenyl)amino]-9,9'-spirobifluorene	Feiming Chemical Limited
18	Spiro-MeO-TPD		2,7-bis[<i>N,N</i> -bis(4-methoxy-phenyl)amino]9,9'-spirobifluorene	Lumtec
19	TAPC		1,1-bis[4-(<i>N,N</i> -di- <i>p</i> -tolylamino)phenyl]cyclohexane	Sensient
20	TCTA		4,4',4''-tris(carbazol-9-yl)-triphenylamine	Sensient
21	TPDP		2,2',6,6'-tetraphenyl-4,4'-bipyranilidene	TU Dresden
22	TPDP-Me		2,2',6,6'-tetra- <i>p</i> -tolyl-4,4'-bipyranilidene	TU Dresden

23	TPDP-OMe		2,2',6,6'-tetrakis(4-methoxyphenyl)-4,4'-bipyranilidene	TU Dresden
24	ZnPc		zinc-phthalocyanine	CreaPhys GmbH

Supplementary Table 3 | Characteristic jV -Parameters of the Low-Donor-Content OSCs. C_{60} is the acceptor (94 mol%) and the donor was changed according to the list. The energy of the charge transfer (CT) state (E_{CT}) and the relaxation energy (λ_s) were obtained by fitting the low energy region of the sensitive EQE_{PV} spectra which corresponds to the CT absorption. The corresponding error bars are obtained by a systematic variation of the fitting range. The ideal V_{OC} under the assumption of only radiative recombination ($V_{OC,rad}$) was calculated from the EQE_{PV} spectra, assuming the reciprocity relation between absorption and emission^{1,14}. The listed values correspond to illumination with simulated sunlight at an intensity of 1000 W/m².

Donor	j_{sc} (mA/cm ²)	FF (%)	PCE (%)	V_{OC} (mV)	$V_{OC,rad}$ (mV)	E_{CT} (meV)	λ_s (meV)
2-TNATA	1.2	32	0.2	409	833	1011±1	417±13
4P-TPD	5.3	51	2.7	990	1341	1576±4	187±13
α -6T	5.7	54	2.9	939	1269	1500±2	282±14
BDTA-BT	0.7	30	0.1	358	840	999±3	475±35
BDTA-DTP	0.3	31	0.01	108	630	751±10	532±77
BF-DBP	4.4	42	1.5	795	1131	1342±2	202±6
BPAPF	4.4	48	2.1	998	1318	1548±3	175±10
BP-Bodipy	6.8	49	2.9	870	1193	1453±1	125±4
DH4T	5.4	47	2.3	921	1291	1516±2	234±13
DH6T	5.6	49	2.5	897	1213	1444±2	281±19
DMFL-NPD	3.5	34	0.8	686	1062	1272±2	230±5
MeO-TPD	3.6	38	0.8	612	989	1195±2	193±8
m-MTDATA	1.1	32	0.1	358	787	954±1	407±16
P4-Ph4-DIP	5.6	46	2.6	1010	1373	1608±1	103±4
Rubrene	5.2	51	2.4	896	1243	1464±1	80±3
Rubrene D ₂₈	5.2	51	2.4	892	1244	1460±1	82±3

Spiro-MeO-TAD	2.4	34	0.5	568	953	1149±3	258±13
Spiro-MeO-TPD	3.0	33	0.5	527	939	1132±3	232±12
TAPC	5.2	58	2.7	907	1230	1448±1	159±6
TCTA	4.5	40	1.8	988	1313	1507±5	199±13
TPDP	0.8	40	0.1	256	761	913±1	164±5
TPDP-Me	0.7	39	0.04	165	698	821±1	146±7
TPDP-OMe	0.6	32	0.02	95	664	752±3	133±20
ZnPc	5.1	39	1.6	788	1103	1369±2	278±10

Supplementary Table 4 | Information to Small Molecule OSCs. The listed OSCs comprise D-A blends (mixing ratio is provided) or planar stacked of D and A. The energy of the charge transfer (CT) state (E_{CT}) was obtained by fitting the low energy region of the sensitive EQE_{PV} spectra which corresponds to the CT absorption. The ideal V_{OC} under the assumption of only radiative recombination ($V_{OC,rad}$) was calculated from the EQE_{PV} spectra, using the reciprocity relation between absorption and emission^{1, 14}. The PCE and the V_{OC} correspond to illumination with simulated sunlight at an intensity of 1000 W/m².

No.	Donor	Acceptor	Stoichiometry D:(D+A) (wt%)	PCE (%)	V_{OC} (mV)	$V_{OC,rad}$ (mV)	E_{CT} (meV)	Ref.
BHJ (bulk heterojunction)								
1	α -6T	C ₆₀	1	1.4	0.98	1.35	1.55	-
2	α -6T	C ₆₀	5	2.8	0.93	1.26	1.49	-
3	α -6T	C ₆₀	7	3.2	0.92	1.24	1.48	-
4	α -6T	C ₆₀	19	2.0	0.81	1.20	1.45	-
5	α -6T	C ₆₀	40	0.9	0.46	0.92	1.08	-
6	α -6T	C ₆₀	68	0.9	0.45	0.90	1.08	-
7	BDTA-BT	C ₆₀	10	< 0.1	0.31	0.84	1.02	-
8	BDTA-BT	C ₆₀	20	< 0.1	0.28	0.84	1.05	-
9	BDTA-DTP	C ₆₀	10	< 0.1	0.04	0.59	0.73	-
10	BDTA-DTP	C ₆₀	20	< 0.1	0.03	0.58	0.73	-
11	BF-DPB	C ₆₀	5	1.1	0.80	1.14	1.34	-
12	BPAPF	C ₆₀	5	1.3	1.00	1.33	1.55	-
13	CNTF	C ₆₀	50	1.2	0.88	1.15	1.47	²³
14	CNV301-5T	C ₆₀	66	2.8	0.98	1.31	1.54	-
15	CuPc	C ₆₀	50	1.6	0.48	0.90	1.13	-
16	DCV ₂ -4T	C ₆₀	50	2.8	0.94	1.30	1.45	-
17	DCV ₂ -4T	C ₆₀	66	3.0	0.98	1.32	1.46	²⁴
18	DCV ₂ -4T-Et(1,1,4,4)	C ₆₀	66	1.2	1.03	1.35	1.54	-
19	DCV ₂ -5T-Me(1,1,5,5)	C ₆₀	66	4.5	0.86	1.21	1.42	²⁵
20	DCV ₂ -5T-Me(2,2,4,4)	C ₆₀	66	3.6	0.85	1.25	1.46	²⁵

21	DCV ₂ -5T-Me(3,3)	C ₆₀	66	6.9	0.96	1.25	1.47	²⁶
22	DCV ₂ -6T-Bu(1,2,5,6)	C ₆₀	66	2.7	0.89	1.20	1.43	-
23	DTDCTB	C ₆₀	50	2.6	0.82	1.13	1.52	-
24	F ₄ ZnPc	C ₆₀	50	3.0	0.73	1.11	1.48	-
25	HAT(CN) ₆	C ₆₀	5	1.8	0.95	1.29	1.55	-
26	m-MTDATA	C ₆₀	5	0.8	0.38	0.80	0.97	-
27	PRTF	C ₆₀	50	2.4	0.90	1.16	1.48	²³
28	Spiro-MeO-TPD	C ₆₀	5	0.9	0.55	0.95	1.13	-
29	TAPC	C ₆₀	1	1.1	0.92	1.28	1.46	-
30	TAPC	C ₆₀	10	2.3	0.87	1.21	1.44	-
31	TAPC	C ₆₀	20	1.4	0.83	1.19	1.45	-
32	TAPC	C ₆₀	50	0.1	0.76	1.19	1.46	-
33	TFTF	C ₆₀	50	1.3	0.82	1.14	1.47	²³
34	TPDP	C ₆₀	20	<0.1	0.13	0.69	0.89	-
35	TPDP	C ₆₀	33	<0.1	0.08	0.65	0.85	-
36	TPDP	C ₆₀	50	<0.1	0.03	0.64	0.83	-
37	TPDP	C ₆₀	66	<0.1	0.07	0.68	0.88	-
38	ZnF ₄ Pc	C ₆₀	50	0.6	0.89	1.21	1.54	-
39	ZnPc	C ₆₀	50	2.7	0.56	0.93	1.18	-
PHJ (planar heterojunction)								
40	BF-DPB	C ₆₀	PHJ	1.1	0.74	1.13	1.31	-
41	BPAPF	C ₆₀	PHJ	1.3	0.93	1.27	1.46	-
42	CuPc	C ₆₀	PHJ	0.8	0.30	0.85	1.02	-
43	DBP	C ₆₀	PHJ	2.6	0.83	1.23	1.41	-
44	ZnPc	C ₆₀	PHJ	0.9	0.41	0.89	1.06	-

Supplementary Table 5 | Information to Polymer OSCs. The listed OSCs comprise D-A blend with polymeric donor molecules. The energy of the charge transfer (CT) state (E_{CT}) was obtained by fitting the low energy region of the sensitive EQE_{PV} spectra which corresponds to the CT absorption. The ideal V_{OC} under the assumption of only radiative recombination ($V_{OC,rad}$) was calculated from the EQE_{PV} spectra, using the reciprocity relation between absorption and emission^{1, 14}. The PCE and the V_{OC} correspond to illumination with simulated sunlight at an intensity of 1000 W/m².

No.	Donor	Acceptor	Stoichiometry D:(D+A) (wt%), comment	PCE (%)	V_{OC} (mV)	$V_{OC,rad}$ (mV)	E_{CT} (meV)	Ref.
The EQE_{PV} spectra of published polymer OSCs were re-analysed with respect to their non-radiative voltage losses. Further details on the OSCs can be found in the corresponding reference.								
1	APFO ₃	PC ₆₁ BM	20	<0.5	1.05	1.38	1.64	1
2	APFO ₃	PC ₆₁ BM	50	~2.0	1.08	1.46	1.66	27
3	APFO ₃	PC ₆₁ BM	80	~4.0	1.16	1.48	1.66	27
4	APFO ₃	PC ₇₁ BM	20	<0.5	0.98	1.39	1.63	27
5	APFO ₃	PC ₇₁ BM	50	~2.0	1.00	1.41	1.66	27
6	Dihexyl-PTV	PC ₆₁ BM	50	0.5	0.57	1.02	1.22	28
7	High-Tg-PPV	PC ₆₁ BM	20	1.0	0.82	1.20	1.44	28
8	LBPP5	PC ₇₁ BM	20	~3.0	0.73	1.14	1.39	27
9	MDMO-PPV	PC ₆₁ BM	20	1.7	0.84	1.15	1.41	1
10	MDMO-PPV	PC ₆₁ BM	50	0.7	0.88	1.22	1.47	28
11	MDMO-PPV	PC ₆₁ BM	80	<0.1	0.92	1.27	1.53	27
12	MDMO-PPV	PC ₆₁ BM	90	<0.1	0.91	1.27	1.53	28
13	MDMO-PPV	PC ₆₁ BM	95	<0.1	0.97	1.28	1.52	28
14	OC9-PEO-PPV	PC ₆₁ BM	20	0.7	0.65	1.13	1.34	28
15	P34T	PC ₆₁ BM	50, f=20%	~1.0	0.49	0.97	1.18	29
16	P34T	PC ₆₁ BM	50, f=51%	~2.0	0.47	0.93	1.15	29
17	P35T	PC ₆₁ BM	50, f=27%	~2.0	0.57	0.99	1.21	29
18	P35T	PC ₆₁ BM	50, f=38%	~3.0	0.50	0.96	1.18	29
19	P35T	PC ₆₁ BM	50, f=51%	~3.0	0.50	0.95	1.17	29
20	P35T	PC ₆₁ BM	50, f=63%	~2.0	0.50	0.93	1.15	29
21	P36T	PC ₆₁ BM	50, f=14%	~3.0	0.63	1.06	1.24	29
22	P36T	PC ₆₁ BM	50, f=34%	~3.0	0.61	1.05	1.22	29
23	P36T	PC ₆₁ BM	50, f=42%	~3.0	0.60	1.05	1.21	29
24	P36T	PC ₆₁ BM	50, f=49%	~2.5	0.58	1.02	1.20	29
25	P3HT	PC ₆₁ BM	50, as cast	1.1	0.76	1.10	1.37	27
26	P3HT	PC ₆₁ BM	50, annealed	2.7	0.62	1.04	1.20	27
27	ReRa-P3HT	PC ₆₁ BM	50	0.2	0.87	1.20	1.47	28
28	PBDTPD	PC ₇₁ BM	40	7.3	0.94	1.34	1.54	30
29	PCDTBT	PC ₇₁ BM	25	4.1	0.87	1.26	1.48	-
30	PCPDTBT	PC ₇₁ BM	33	2.5	0.67	1.05	1.29	27

31	PCPDTBT	PC ₇₁ BM	33, with ODT	5.5	0.64	1.01	1.25	27
32	TQm6	PC ₇₁ BM	25	4.3	0.86	1.17	1.45	31
33	TQm8	PC ₇₁ BM	25	5.0	0.87	1.22	1.48	31
34	TQmEH	PC ₇₁ BM	25	2.9	0.80	1.14	1.43	31
35	TQp6	PC ₇₁ BM	50	0.5	0.52	1.00	1.21	31
36	TQp8	PC ₇₁ BM	33	1.9	0.65	1.06	1.27	31
37	TQp12	PC ₇₁ BM	25	1.8	0.76	1.09	1.31	31
Values which were taken from recent publications:								
38	DTD	N2200	50	3.7	0.84	1.16	1.42	32
39	PIPCP	PC ₆₁ BM	33	6.4	0.89	1.16	1.46 ^a	18
40	PIDTT-TID	PC ₇₁ BM	25	6.7	1.00	1.24	1.57 ^b	20
41	P3TEA	SF-PDI ₂	40	9.5	1.37	1.37	1.72	2

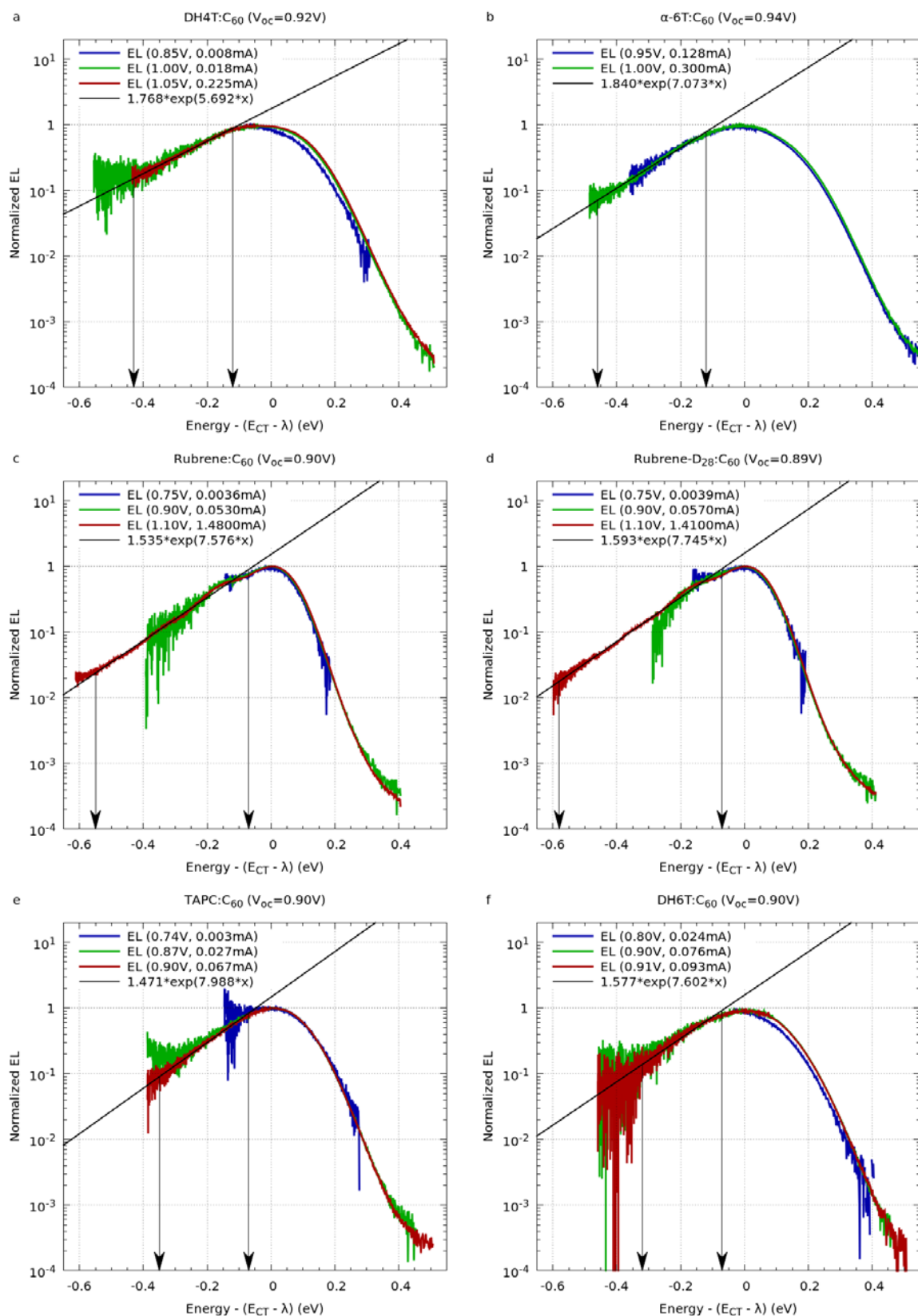
Supplementary Table 6 | Fit of ΔV_{nr} as a Function of $(E_{CT}-\lambda_s)$ and of EL as a Function of the Photon-Energy. The fit values corresponding to Figure 3a are listed for the trend obtained from EQE_{PV} and EQE_{EL} . To compare the non-radiative voltage losses and the slope of the emission intensity, we apply the function $\frac{k_B T}{q} \ln(\text{emission}) = a + b \cdot (E - (E_{CT} - \lambda_s))$, thus it follows $a = \frac{k_B T}{q} \ln(A')$ and $b = \frac{k_B T}{q} B$, in comparison to the fits applied in Supplementary Figure 6.

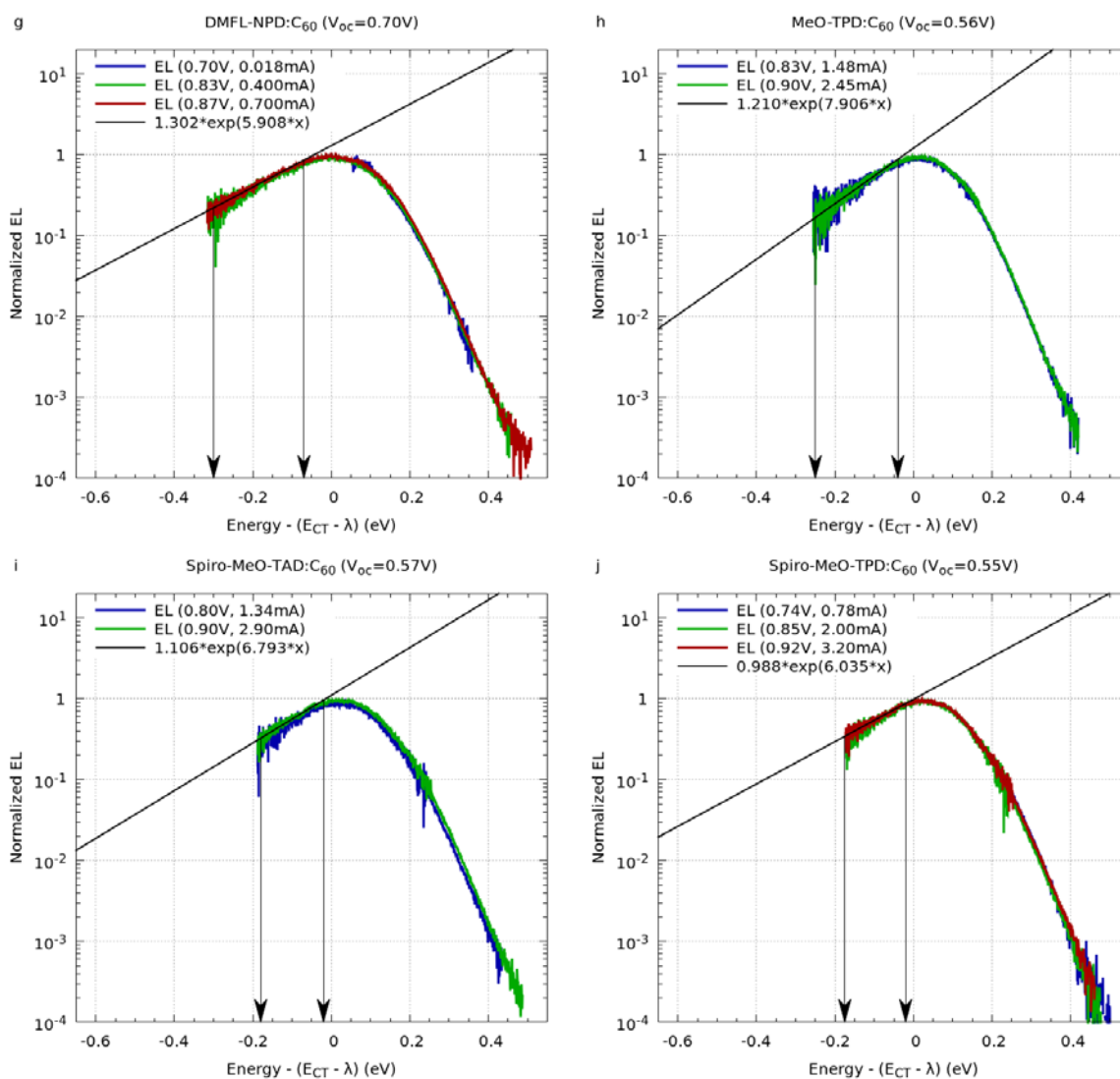
x-axis (eV)	y-axis (mV)	data set	$y = a + b \cdot x$	
			$a \pm \text{error } a$ (mV)	$b \pm \text{error } b$ (mV/eV)
$E_{CT} - \lambda_s$	ΔV_{nr}	low-donor	574.3 ± 27.4	-184.3 ± 25.8
$E_{CT} - \lambda_s$	ΔV_{nr}	low-donor EQE_{EL}	556.1 ± 19.2	-192.9 ± 16.3
$E - (E_{CT} - \lambda_s)$	$\frac{k_B T}{q} \ln(\text{emission})$	selected EL spectra ($n=10$)	8.8 ± 5.2	178.2 ± 22.2

^a Consistently to our elaboration of the data, E_{CT} should amount 1.46 eV. At this CT state energy both emission and absorption clearly cross.

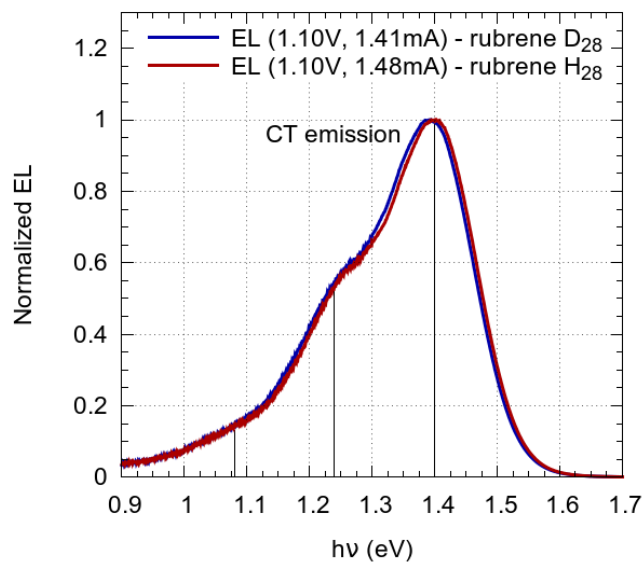
^b The E_{CT} value was originally not provided in this publication. Here, E_{CT} is obtained from the EL spectrum which is shown in the paper and is in good agreement with the EQE_{PV} spectrum.

Supplementary Figures





Supplementary Figure 6 | Slope of the Low Energy CT State Emission. Electroluminescence of different donor:C₆₀ CT states as a function of the photon-energy shifted by the peak of emission ($E_{CT} - \lambda_s$). The low energy tail is fitted by $y = A' \exp(B \cdot (E - (E_{CT} - \lambda_s)))$. The x-range where the fit is applied is indicated by arrows. The low energy emission of all CT states has a similar slope (value of B).



Supplementary Figure 7 | CT State Emission of Rubrene and Deuterated Rubrene. Electroluminescence of the CT state of C₆₀:rubrene and C₆₀:rubrene-D₂₈ as a function of the photon-energy. The low energy tail of the CT state emission for both D-A interfaces has the same sub-structure.

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